FW297

Power MOSFET 60V, 58mΩ, 4.5A, Dual N-Channel



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Features

- Low On-Resistance
- 4.0V Drive
- ESD Diode-Protected Gate
- Pb-Free, Halogen Free and RoHS Compliance

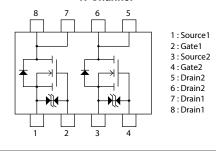
	VDSS	KDS(on) Max	^I D Max
	60V	58mΩ@ 10V	
		84mΩ@ 4.5V	4.5A
		95mΩ@ 4.0V	

Specifications

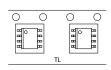
Absolute Maximum Ratings at Ta = 25°C

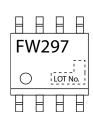
Parameter	Symbol	Value	Unit
Drain to Source Voltage	V _{DSS}	60	V
Gate to Source Voltage	VGSS	±20	V
Drain Current (DC)	ID	4.5	Α
Drain Current (Pulse) PW ≤ 10μs, duty cycle ≤ 1%	I _{DP}	18	А
Power Dissipation When mounted on ceramic substrate (2000mm² × 0.8mm) 1 unit, PW≤10s	PD	1.8	W
Total Dissipation When mounted on ceramic substrate (2000mm²×0.8mm), PW≤10s	PŢ	2.2	W
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	-55 to +150	°C

Electrical Connection N-Channel



Packing Type: TL Marking





Thermal Resistance Ratings

Parameter	Symbol	Value	Unit
Junction to Ambient 1 unit, PW≤10s *1	$R_{\theta JA}$	69.4	0000
Junction to Ambient 2 units, PW≤10s *1	$R_{\theta JA}$	56.8	°C/W

Note: *1 When mounted on ceramic substrate (2000mm² × 0.8mm)

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

ORDERING INFORMATION

See detailed ordering and shipping information on page 5 of this data sheet.

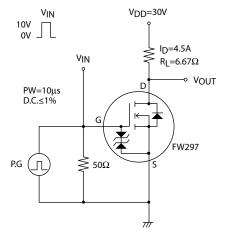
FW297

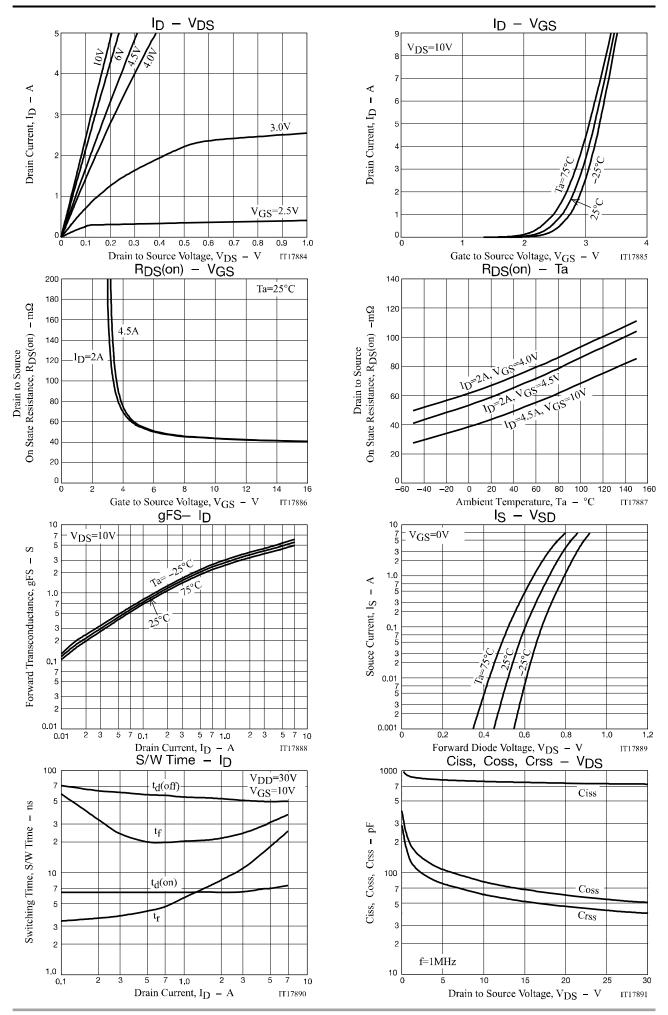
Electrical Characteristics at Ta = 25°C

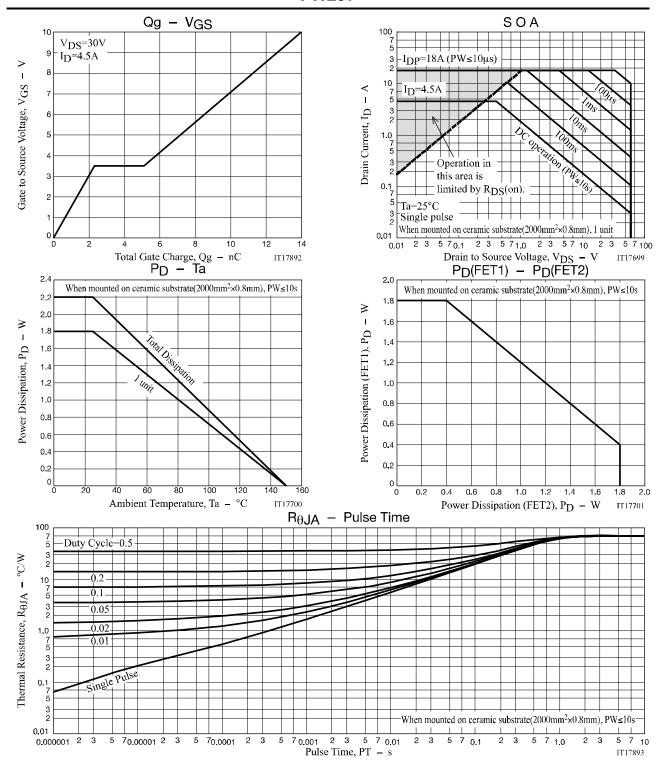
Ptu	Symbol	0 111		Value		
Parameter		Conditions	min	typ	max	Unit
Drain to Source Breakdown Voltage	V(BR)DSS	I _D =1mA, V _{GS} =0V	60			V
Zero-Gate Voltage Drain Current	I _{DSS}	V _{DS} =60V, V _{GS} =0V			1	μΑ
Gate to Source Leakage Current	IGSS	V _{GS} =±16V, V _{DS} =0V			±10	μΑ
Gate Threshold Voltage	V _{GS} (th)	V _{DS} =10V, I _D =1mA	1.2		2.6	V
Forward Transconductance	9FS	V _{DS} =10V, I _D =4.5A		4.7		S
	R _{DS} (on)1	I _D =4.5A, V _{GS} =10V		45	58	mΩ
Static Drain to Source On-State Resistance	R _{DS} (on)2	I _D =2A, V _{GS} =4.5V		60	84	mΩ
	R _{DS} (on)3	I _D =2A, V _{GS} =4.0V		68	95	mΩ
Input Capacitance	Ciss			750		pF
Output Capacitance	Coss	V _{DS} =20V, f=1MHz		59		pF
Reverse Transfer Capacitance	Crss			47		pF
Turn-ON Delay Time	t _d (on)			7		ns
Rise Time	t _r	See specified Test Circuit		16		ns
Turn-OFF Delay Time	t _d (off)			50		ns
Fall Time	tf			30		ns
Total Gate Charge	Qg	V _{DS} =30V, V _{GS} =10V, I _D =4.5A		14		nC
Gate to Source Charge	Qgs			2.3		nC
Gate to Drain "Miller" Charge	Qgd]		2.8		nC
Forward Diode Voltage	V _{SD}	I _S =4.5A, V _{GS} =0V		0.81	1.2	V

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

Switching Time Test Circuit







Package Dimensions

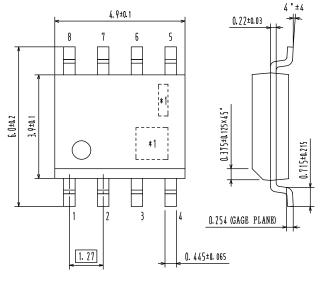
FW297-TL-2W

SOIC-8

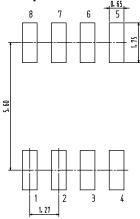
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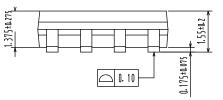
Unit: mm

- 1: Source1
- 2: Gate1
- 3: Source2
- 4: Gate2
- 5: Drain2
- 6: Drain2
- 7: Drain1
- 8: Drain1



Recommended Soldering Footprint





*1:Lot indication

ORDERING INFORMATION

Device	Package	Shipping	Note	
FW297-TL-2W	SOIC8 SC-87, SOT-96	2,500 pcs. / Tape & Reel	Pb-Free and Halogen Free	

[†] For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D. http://www.onsemi.com/pub_link/Collateral/BRD8011-D.PDF

Note on usage: Since the FW297 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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